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PREFACE

This volume contains papers presented at Symposium E, "Doping Engineering for Front-End Processing," held March 25–27 at the 2008 MRS Spring Meeting in San Francisco, California. The scope of the symposium was to bring together researchers from the field of materials science and technology to review the state-of-the-art in doping engineering and activation methods, metal-semiconductors contacting for integrated circuits, to discuss the current achievements, remaining challenges, and to identify future research directions for fundamental investigation and technology development. These proceedings document the recent developments in the areas of experiments, modeling and metrology related to planar and FIN transistor source and drain regions.

It has been a pleasure and privilege to have the opportunity to organize the symposium and edit this volume. This would not be possible without the support of the speakers and authors, all of whom are gratefully acknowledged.

Many exciting research achievements have been presented at this symposium. We hope that the readers will enjoy reading this proceedings volume, and find its contents both informative and interesting.

B.J. Pawlak
M.L. Pelaz
M. Law
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July 2008

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